TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2993

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & \text{Low drain-source ON resistance} & : R_{DS} \ (\text{ON}) = 82 \ \text{m}\Omega \ (\text{typ.}) \\ \bullet & \text{High forward transfer admittance} & : |Y_{fs}| = 20 \ \text{S (typ.}) \\ \bullet & \text{Low leakage current} & : I_{DSS} = 100 \ \mu\text{A (max)} \ (V_{DS} = 250 \ \text{V}) \\ \bullet & \text{Enhancement mode} & : V_{th} = 1.5 \text{\sim} 3.5 \ \text{V (V}_{DS} = 10 \ \text{V, I}_{D} = 1 \ \text{mA}) \\ \end{array}$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	250	V	
Drain-gate voltage (Ro	_{SS} = 20 kΩ)	V_{DGR}	250	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	20	Α	
	Pulse (Note 1)	I _{DP}	60		
Drain power dissipation	n (Tc = 25°C)	P_{D}	100	W	
Single pulse avalanche	e energy (Note 2)	E _{AS}	423	mJ	
Avalanche current		I _{AR}	20	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	10	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.25	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

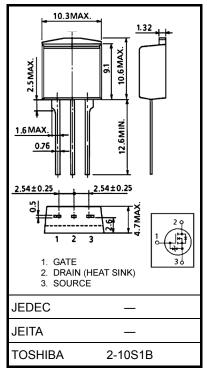
Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 1.79 mH, I_{AR} = 20 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

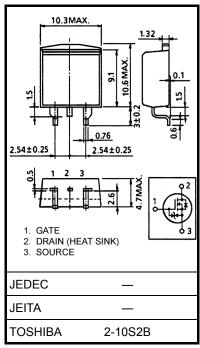
This transistor is an electrostatic-sensitive device.

Please handle with caution.

Unit: mm



Weight: 1.5 g (typ.)



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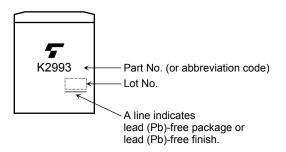
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	irrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μA
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	250	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 10 A	_	82	105	mΩ
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	10	20	_	S
Input capacitano	e	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		4000	_	pF
Reverse transfe	r capacitance	C _{rss}			300	_	
Output capacita	nce	Coss			1000	_	
Switching time	Rise time	t _r	V _{GS} _{0V}	_	15	_	ns
	Turn-on time	t _{on}		_	35	_	
	Fall time	t _f		_	30	_	
	Turn-off time	t _{off}	$V_{DD} \stackrel{.}{=} 130V$ Duty $\leq 1\%$, $t_w = 10 \mu s$	_	180	_	
Total gate charg plus gate-drain)		Qg		_	100	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 200 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		70	_	nC
Gate-drain ("miller") charge Q _{gd}		Q _{gd}		_	30	_	

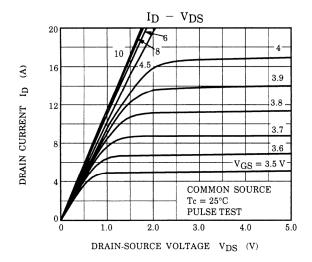
Source-Drain Ratings and Characteristics (Ta = 25°C)

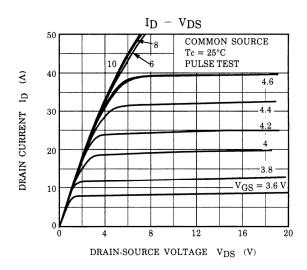
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	20	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	60	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-2.0	V
Reverse recovery time	t _{rr}	I _{DR} = 20 A, V _{GS} = 0 V		300	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 Å / μs	_	3.3	_	μC

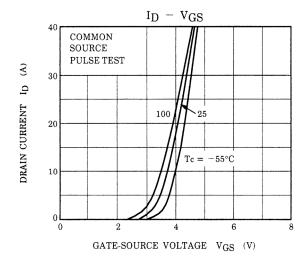
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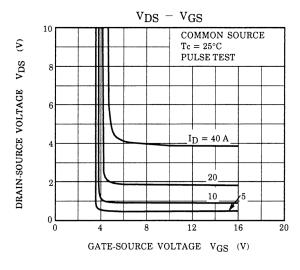


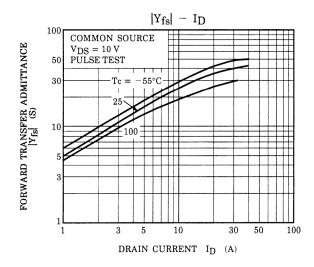
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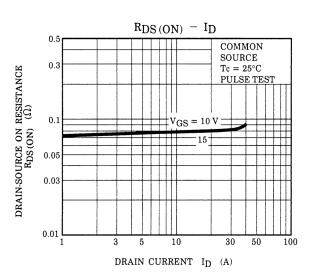


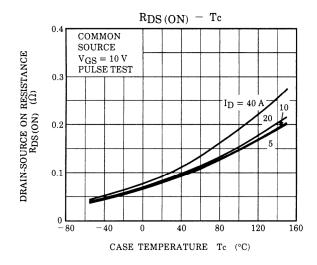


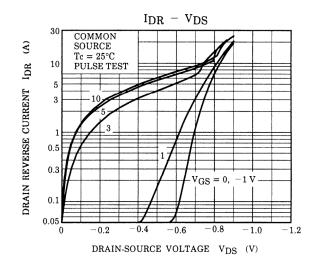


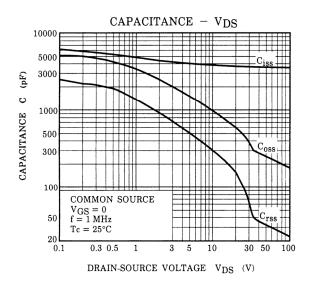


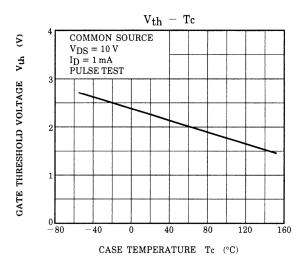


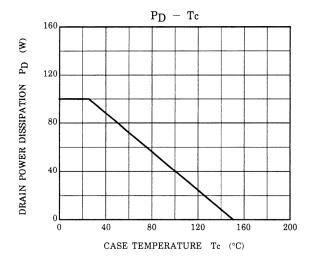


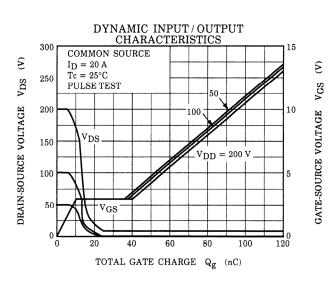


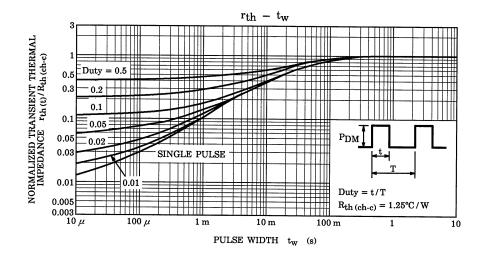


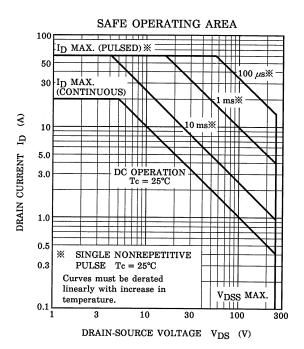


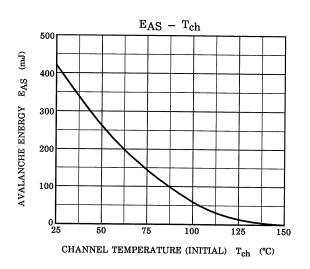


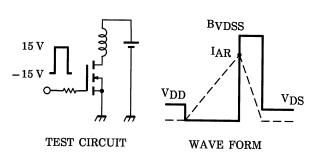












$$\begin{aligned} &RG = 25~\Omega \\ &V_{DD} = 90~V,~L = 1.79~mH \end{aligned} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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20070701-EN

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